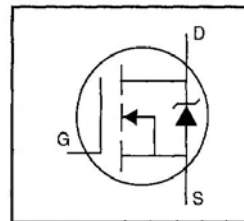


# IRLD024PbF

## HEXFET® Power MOSFET

- Dynamic  $dv/dt$  Rating
- For Automatic Insertion
- End Stackable
- Logic-Level Gate Drive
- $R_{DS(on)}$  Specified at  $V_{GS}=4V$  &  $5V$
- $175^{\circ}C$  Operating Temperature
- Fast Switching
- Lead-Free

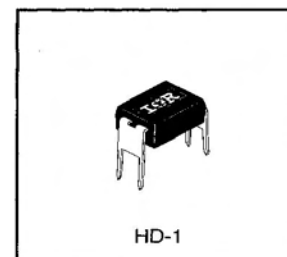


$V_{DSS} = 60V$   
 $R_{DS(on)} = 0.10\Omega$   
 $I_D = 2.5A$

## Description

Third Generation HEXFETs from International Rectifier provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The 4-pin DIP package is a low cost machine-insertable case style which can be stacked in multiple combinations on standard 0.1 inch pin centers. The dual drain serves as a thermal link to the mounting surface for power dissipation levels up to 1 watt.



## Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^{\circ}C$	Continuous Drain Current, $V_{GS} @ 5.0 V$	2.5	A
$I_D @ T_C = 100^{\circ}C$	Continuous Drain Current, $V_{GS} @ 5.0 V$	1.8	
$I_{DM}$	Pulsed Drain Current ①	20	
$P_D @ T_C = 25^{\circ}C$	Power Dissipation	1.3	W
	Linear Derating Factor	0.0083	W/ $^{\circ}C$
$V_{GS}$	Gate-to-Source Voltage	$\pm 10$	V
$E_{AS}$	Single Pulse Avalanche Energy ②	91	mJ
$dv/dt$	Peak Diode Recovery $dv/dt$ ③	4.5	V/ns
$T_J$ $T_{STG}$	Operating Junction and Storage Temperature Range	-55 to +175	$^{\circ}C$
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

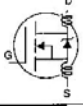
## Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JA}$	Junction-to-Ambient	—	—	120	$^{\circ}C/W$

# IRLD024PbF

International  
IR Rectifier

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	60	—	—	V	$V_{GS}=0V, I_D=250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.060	—	$V/^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D=1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.10	$\Omega$	$V_{GS}=5.0V, I_D=1.5A$ ④
		—	—	0.14		$V_{GS}=4.0V, I_D=1.3A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	2.0	V	$V_{DS}=V_{GS}, I_D=250\mu A$
$g_{fs}$	Forward Transconductance	3.7	—	—	S	$V_{DS}=25V, I_D=1.5A$ ④
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	25	$\mu A$	$V_{DS}=60V, V_{GS}=0V$
		—	—	250		$V_{DS}=48V, V_{GS}=0V, T_J=150^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS}=10V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS}=-10V$
$Q_g$	Total Gate Charge	—	—	18	nC	$I_D=17A$
$Q_{gs}$	Gate-to-Source Charge	—	—	4.5		$V_{DS}=48V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	—	12		$V_{GS}=5.0V$ See Fig. 6 and 13 ④
$t_{d(on)}$	Turn-On Delay Time	—	11	—	ns	$V_{DD}=30V$
$t_r$	Rise Time	—	110	—		$I_D=17A$
$t_{d(off)}$	Turn-Off Delay Time	—	23	—		$R_G=9.0\Omega$
$t_f$	Fall Time	—	41	—		$R_D=1.7\Omega$ See Figure 10 ④
$L_D$	Internal Drain Inductance	—	4.0	—	nH	Between lead, 6 mm (0.25in.) from package and center of die contact
$L_S$	Internal Source Inductance	—	6.0	—		
$C_{iss}$	Input Capacitance	—	870	—	pF	$V_{GS}=0V$
$C_{oss}$	Output Capacitance	—	360	—		$V_{DS}=25V$
$C_{rss}$	Reverse Transfer Capacitance	—	53	—		$f=1.0\text{MHz}$ See Figure 5

## Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	2.5	A	MOSFET symbol showing the integral reverse p-n junction diode.
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	20		
$V_{SD}$	Diode Forward Voltage	—	—	1.5	V	$T_J=25^\circ\text{C}, I_S=2.5A, V_{GS}=0V$ ④
$t_{rr}$	Reverse Recovery Time	—	110	260	ns	$T_J=25^\circ\text{C}, I_F=17A$
$Q_{rr}$	Reverse Recovery Charge	—	0.49	1.5	$\mu\text{C}$	$di/dt=100A/\mu\text{s}$ ④
$t_{on}$	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S+L_D$ )				

### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature (See Figure 11)
- ②  $V_{DD}=25V$ , starting  $T_J=25^\circ\text{C}$ ,  $L=16\text{mH}$   
 $R_G=25\Omega, I_{AS}=2.5A$  (See Figure 12)
- ③  $I_{SD}\leq 17A, di/dt\leq 140A/\mu\text{s}, V_{DD}\leq V_{(BR)DSS}, T_J\leq 175^\circ\text{C}$
- ④ Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

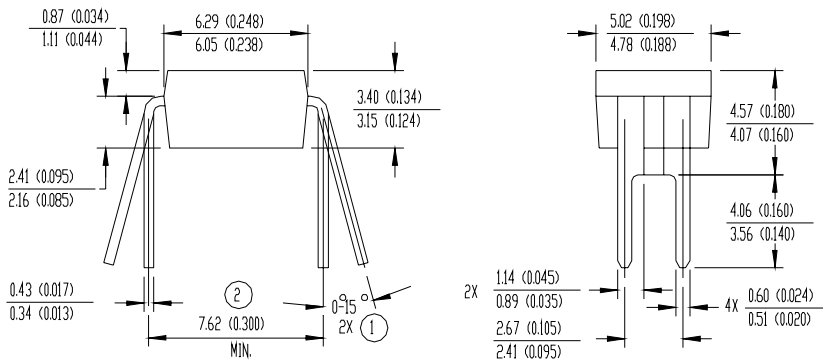
# IRLD024PbF

## Hexdip Package Outline



NOTES:

- ① APPLIES TO SPREAD OF LEADS PRIOR TO INSTALLATION
- ② APPLIES TO INSTALLED LEAD CENTERS
- 3 CONTROLLING DIMENSION: INCH.
- 4 DIMENSIONS ARE SHOWN MILLIMETERS (INCHES).
- 5 CASE STYLE HD-1 (SIMILAR TO JEDEC OUTLINE MO-001AN)
- 6 DIMENSIONS SHOWN ARE BEFORE SOLDER DIP  
SOLDER DIP MAX. + 0.16 (0.006)



## Hexdip Part Marking Information

EXAMPLE: THIS IS AN IRFD120

